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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>			<b>Complete if Known</b>		
			Application Number	10/761369	
			Filing Date	January 22, 2004	
			First Named Inventor	Kristy A. Campbell	
			Art Unit	2818	
			Examiner Name	LONG TRAN	
Sheet	1	of	11	Attorney Docket Number	M4065.0988/P988-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
✓	AA	2002/0000666	1/3/2002	Kozicki et al.	
	AB	2002/0072188	6/13/2002	Gilton	
	AC	2002/0106849	08/08/2002	Moore	
	AH	2002/0123169	09/05/2002	Moore et al.	
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	AJ	2002/0123248	09/05/2002	Moore et al.	
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✓	AU1	3,622,319	11/1971	Sharp	
	AV1	3,743,847	7/1973	Boland	
	AW1	4,269,935	5/1981	Masters et al.	
	AX1	4,312,938	1/1982	Drexler, et al.	
	AY1	4,316,946	1/1982	Masters, et al.	
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Sheet	3	of	11	Attorney Docket Number	M4065.0988/P988-A

UR	AR3	6,316,784	11/2001	Zahorik et al.	
	AS3	6,329,606	12/2001	Freyman et al.	
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	AC4	6,440,837	8/27/2002	Harshfield	
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	AE4	6,473,332	10/2002	Ignatiev et al.	
	AF4	6,487,106	11/26/2002	Kozicki	

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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>2</sup> -Number <sup>3</sup> -Kind Code <sup>4</sup> (if known)					
UR	BA	56126916		10/19981	Akira et al.		
	BB	WO 97/48032		12/18/1997	Kozicki et al.		
	BC	WO 99/28914		06/10/1999	Kozicki et al.		
	BD	WO 00/48196		08/17/2000	Kozicki et al.		
	BE	WO 02/21542		03/14/2002	Kozicki et al.		
	BD	1,187,965		5/1967	Birdseye, et al.		
	BE	2-122501		5/1990			
	BF	59-20913		2/1984			
	BG	50-18597		9/1973			

Examiner Signature		Date Considered	6/17/05
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See attached Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1448A/PTO		<b>Complete if Known</b>			
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		Art Unit			
		Examiner Name			
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
W	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.	
	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.	
	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se <sub>75</sub> Ge <sub>25</sub> -xSbx, Appl. Phys. A 55 (1992) 167-169.	
	CE	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe <sub>1-x</sub> , Egypt, J. Phys. 17 (1986) 335-342.	
	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag <sub>2</sub> Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.	
	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.	
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810	
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	CM	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.	
	CN	Belin, R.; Taillades, G.; Pradel, A.; Ribes, M., Ion dynamics in superionic chalcogenide glasses: complete conductivity spectra, Solid state Ionics 136-137 (2000) 1025-1029.	
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	CP	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.	
	CQ	Bernede, J.C., Influence du metal des electrodes sur les caracteristiques courant-tension des structures M-Ag <sub>2</sub> Se-M, Thin solid films 70 (1980) L1-L4.	
	CR	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.	
	CS	Bernede, J.C., Switching and silver movements in Ag <sub>2</sub> Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.	
	CT	Bernede, J.C., Commutations dans les couches minces de selenium, Phys. Stat. Vol. (a), 97-102 (1981).	
	CU	Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin solid films 131 (1985) L61-L64.	
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✓	CW	Bernede, J.C.; Khelil, A.; Kettaf, M.; Conan, A., Transition from S- to N-type differential negative resistance in Al-Al <sub>2</sub> O <sub>3</sub> -Ag <sub>2</sub> -xSe <sub>1+x</sub> thin film structures, Phys. Stat. Sol. (a) 74 (1982) 217-224.	
	CX	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg <sub>4</sub> I <sub>5</sub> , Solid State Ionics 70/71 (1994) 72-76.	
	CY	Boolchand, P., The maximum in glass transition temperature (T <sub>g</sub> ) near x=1/3 in GexSe <sub>1-x</sub> Glasses, Asian Journal of Physics (2000) 9, 709-72.	
	CZ	Boolchand, P.; Bresser, W.J., Mobile silver ions and glass formation in solid electrolytes, Nature 410 (2001) 1070-1073.	
	CA1	Boolchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703	
	CB1	Boolchand, P.; Selvanathan, D.; Wang, Y.; Georgiev, D.G.; Bresser, W.J., Onset of rigidity in steps in chalcogenide glasses, Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132.	
	CC1	Boolchand, P.; Enzweiler, R.N.; Tenhover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420.	
	CD1	Boolchand, P.; Grothaus, J.; Bresser, W.J.; Suranyi, P., Structural origin of broken chemical order in a GeSe <sub>2</sub> glass, Phys. Rev. B 25 (1982) 2975-2978.	
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	CK1	Cohen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe <sub>2</sub> Crystals, Science 258 (1992) 271-274.	
	CL1	Chatterjee, R.; Asokan, S.; Titus, S.S.K., Current-controlled negative-resistance behavior and memory switching in bulk As-Te-Se glasses, J. Phys. D: Appl. Phys. 27 (1994) 2624-2627.	
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	CO1	Chen, G.; Cheng, J.; Chen, W., Effect of Si <sub>3</sub> N <sub>4</sub> on chemical durability of chalcogenide glass, J. Non-Cryst. Solids 220 (1997) 249-253.	
	CP1	Cohen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891.	
	CQ1	Croitoru, N.; Lazarescu, M.; Popescu, C.; Telnic, M.; and Vescan, L., Ohmic and non-ohmic conduction in some amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 781-786.	
	CR1	Dalven, R.; Gill, R., Electrical properties of beta-Ag <sub>2</sub> Te and beta-Ag <sub>2</sub> Se from 4.2 to 300K, J. Appl. Phys. 38 (1967) 753-756.	
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WCT	CT1	Deamaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191.	
	CU1	Dejus, R.J.; Susman, S.; Volin, K.J.; Montague, D.G.; Price, D.L., Structure of Vitreous Ag-Ge-Se, J. Non-Cryst. Solids 143 (1992) 162-180.	
	CV1	den Boer, W., Threshold switching in hydrogenated amorphous silicon, Appl. Phys. Lett. 40 (1982) 812-813.	
	CW1	Drusedau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.	
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	CZ1	El Ghrandi, R.; Calas, J.; Galibert, G.; Averous, M., Silver photodissolution in amorphous chalcogenide thin films, Thin Solid Films 218 (1992) 259-273.	
	CA2	El Ghrandi, R.; Calas, J.; Galibert, G., Ag dissolution kinetics in amorphous GeSe <sub>5.5</sub> thin films from "in-situ" resistance measurements vs time, Phys. Stat. Sol. (a) 123 (1991) 451-460.	
	CB2	El-kady, Y.L., The threshold switching in semiconducting glass Ge <sub>21</sub> Se <sub>17</sub> Te <sub>62</sub> , Indian J. Phys. 70A (1996) 507-516.	
	CC2	Elliott, S.R., A unified mechanism for metal photodissolution in amorphous chalcogenide materials, J. Non-Cryst. Solids 130 (1991) 85-97.	
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	CF2	El-Zahed, H.; El-Korashy, A., Influence of composition on the electrical and optical properties of Ge <sub>20</sub> BixSe <sub>80-x</sub> films, Thin Solid Films 376 (2000) 236-240.	
	CG2	Fadel, M., Switching phenomenon in evaporated Se-Ge-As thin films of amorphous chalcogenide glass, Vacuum 44 (1993) 851-855.	
	CH2	Fadel, M.; El-Shair, H.T., Electrical, thermal and optical properties of Se <sub>75</sub> Ge <sub>7</sub> Sb <sub>18</sub> , Vacuum 43 (1992) 253-257.	
	CI2	Feng, X.; Bresser, W.J.; Boolchand, P., Direct evidence for stiffness threshold in Chalcogenide glasses, Phys. Rev. Lett. 78 (1997) 4422-4425.	
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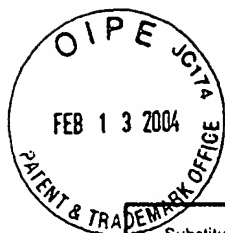
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				First Named Inventor	Kristy A. Campbell
				Art Unit	2818
				Examiner Name	<del>D. M. Nguyen</del> LONG TRAN
Sheet	1	of	1	Attorney Docket Number	M4065.0988/P988-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
UK	AA	US-2003/015589	8/2003	Campbell et al.	
	AB	US-5,825,046	10/1998	Czubatyj et al.	
	AC	US-5,363,329	11/1994	Troyan	
	AD	US-3,753,110	8/1973	Ikeda et al.	
	AE	US-4,115,872	9/1978	Bluhm	
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	AG	US-5,920,788	7/1999	Reinberg	
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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
UK	BA	EP 1 202 285 A2	2/2002	Nishihara et al.		

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<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

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6/17/05



PTO/SB/08a/b (08-03)

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<b>Substitute for form 1449A/B/PTO</b>  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	10/761,369
				Filing Date	January 22, 2004
				First Named Inventor	Kristy A. Campbell
				Art Unit	N/A 2818
				Examiner Name	Not Yet Assigned LONG PAK
Sheet	1	of	1	Attorney Docket Number	M4065.0988/P988-A

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UKT	CA	YOJI KAWAMOTO, et al.; "Ionic Conduction in As <sub>2</sub> S <sub>3</sub> -Ag <sub>2</sub> S, GeS <sub>2</sub> -GeS-Ag <sub>2</sub> S and P <sub>2</sub> S <sub>5</sub> -Ag <sub>2</sub> S Glasses" Journal of Non-Crystalline Solids 20, 393-404 (1976).	

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Examiner Signature		Date Considered	6/17/05
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